

MA160A

Silicon epitaxial planer type

For switching circuits

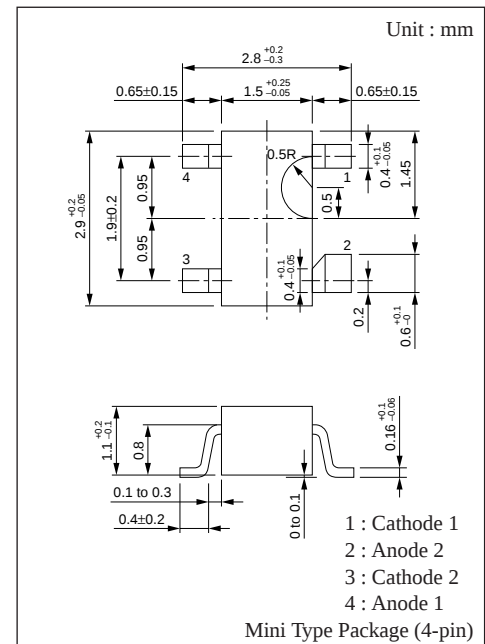
■ Features

- Independent incorporating of two elements, enabling high-density mounting
- Point-symmetrical wiring, without need of taping direction
- Short reverse recovery period t_{rr}
- Small capacity between pins, C_t

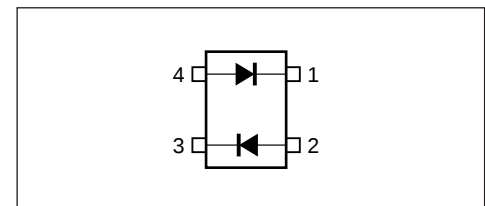
■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Repetitive peak reverse voltage	V_{RRM}	80	V
Average forward current	Single	$I_{F(AV)}$	100
	Double	$I_{F(AV)}$	75
Repetitive peak forward current	Single	I_{FRM}	225
	Double	I_{FRM}	170
Non-repetitive peak forward surge current	Single	I_{FSM}^*	500
	Double	I_{FSM}^*	375
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	- 55 to +150	°C

* $t=1s$



■ Internal Connection

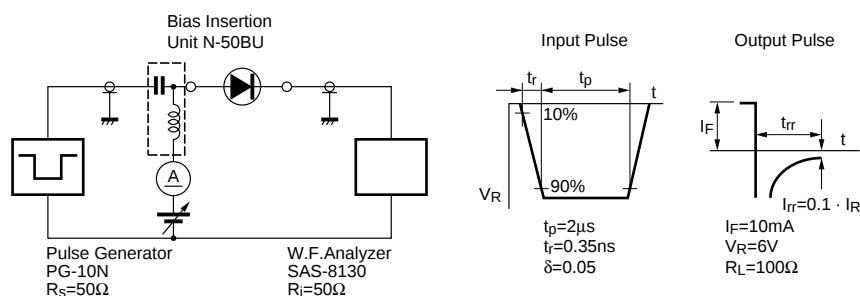


■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R=75V$			0.1	μA
Forward voltage (DC)	V_F	$I_F=100mA$		0.95	1.2	V
Reverse voltage (DC)	V_R	$I_R=100\mu A$	80			V
Terminal capacitance	C_t	$V_R=0V, f=1MHz$		0.9	2	pF
Reverse recovery time	t_{rr}^*	$I_F=10mA, V_R=6V$ $I_{rr}=0.1 \cdot I_R, R_L=100\Omega$			3	ns

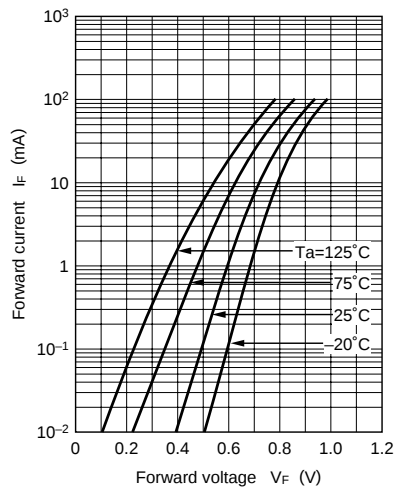
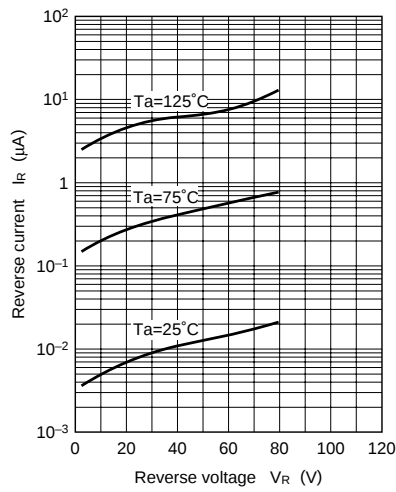
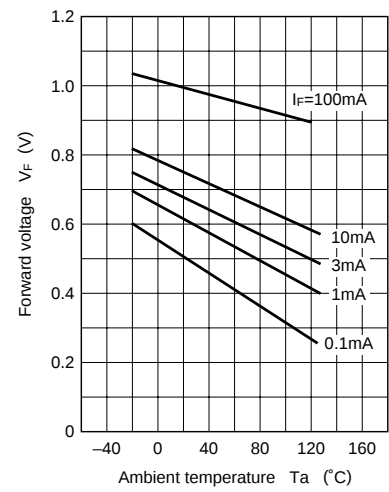
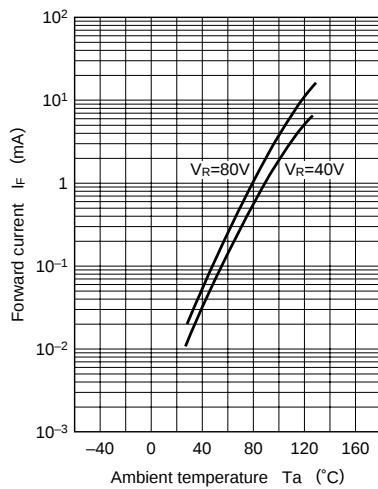
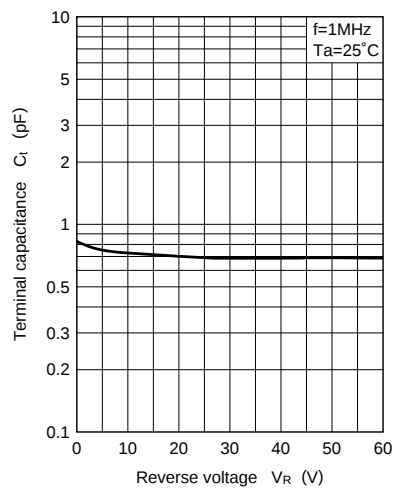
Note 1 : Rated input/output frequency : 100MHz

2 : * t_{rr} measuring circuit



■ Marking (Example)



$I_F - V_F$  $I_R - V_R$  $V_F - T_a$  $I_R - T_a$  $C_t - V_R$  $I_F(\text{surge}) - t_w$ 